

APPENDIX TO AMENDMENT DATED NOVEMBER 21, 2001

AMENDMENTS TO CLAIM 11

11. (Amended) A method for substantially preserving a photoresist while removing exposed areas of an organic ARC during the manufacturing of an integrated circuit comprising exposing the ARC to a system of etching agents in an ionized state in a reaction chamber of a plasma generating device, the system of etching agents being nitrogen-free and including one or more fluorine-containing compounds, an inert carrier gas and chlorine.